



LET21004

RF POWER TRANSISTORS

Ldmos Enhanced Technology in Plastic Package

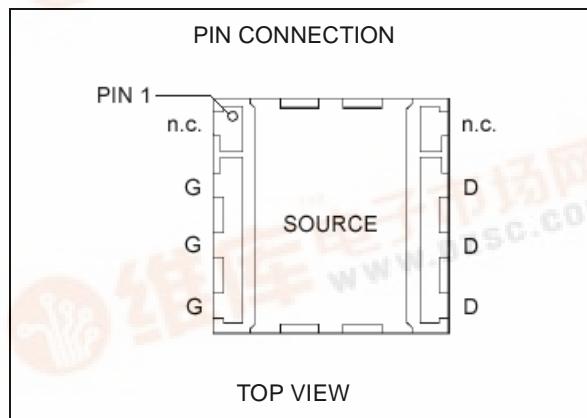
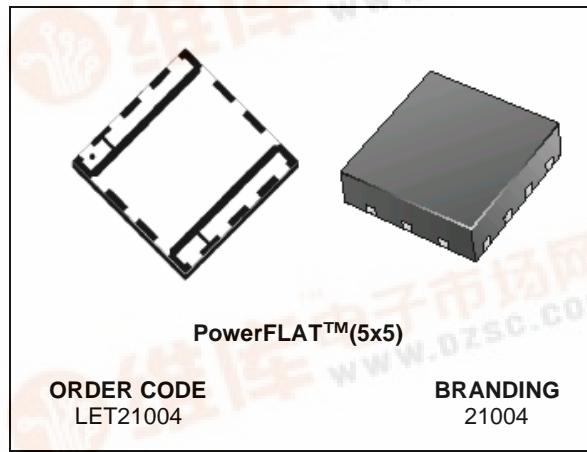
TARGET DATA

Designed for GSM / EDGE / IS-97 / WCDMA applications

- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- $P_{OUT} = 4$ W with 11 dB gain @ 2170 MHz / 26 V
- NEW LEADLESS PLASTIC PACKAGE
- ESD PROTECTION

DESCRIPTION

The LET21004 is a common source N-Channel, enhancement-mode lateral Field-Effect RF power transistor. It is designed for high gain, broad band commercial and industrial applications. It operates at 26 V in common source mode at frequencies up to 2.1 GHz. LET21004 boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in the innovative leadless SMD plastic package, PowerFLAT™. LET21004's superior linearity performance makes it an ideal solution for base station applications.



ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25$ °C)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-Source Voltage	65	V
V_{GS}	Gate-Source Voltage	-0.5 to +15	V
I_D	Drain Current	1	A
P_{DISS}	Power Dissipation (@ $T_c = 70$ °C)	TBD	W
T_j	Max. Operating Junction Temperature	150	°C
T_{STG}	Storage Temperature	-65 to +150	°C

THERMAL DATA ($T_{CASE} = 70$ °C)

$R_{th(j-c)}$	Junction -Case Thermal Resistance	TBD	°C/W
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LET21004

ELECTRICAL SPECIFICATION (T_{CASE} = 25 °C)

STATIC

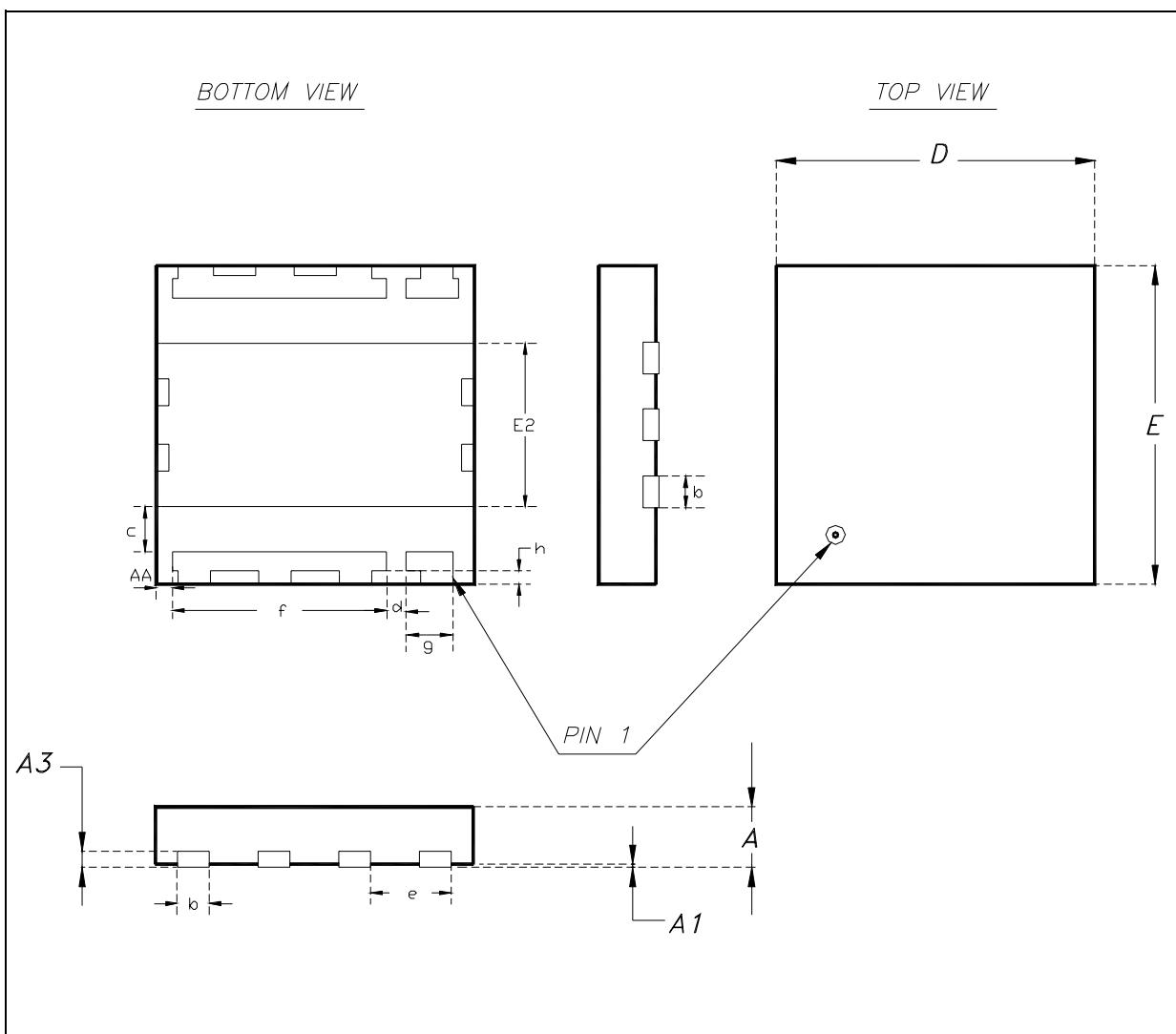
Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V _{(BR)DSS}	V _{GS} = 0 V I _{DS} = 1 mA		65			V
I _{DSS}	V _{GS} = 0 V V _{DS} = 26 V				1	µA
I _{GSS}	V _{GS} = 5 V V _{DS} = 0 V				1	µA
V _{GS(Q)}	V _{DS} = 28 V I _D = TBD		2.5		5.0	V
V _{DS(ON)}	V _{GS} = 10 V I _D = 0.3 A			TBD	0.3	V
G _{FS}	V _{DS} = 10 V I _D = 0.3 A			TBD		mho
C _{ISS}	V _{GS} = 0 V	V _{DS} = 26 V	f = 1 MHz		TBD	pF
C _{OSS}	V _{GS} = 0 V	V _{DS} = 26 V	f = 1 MHz		TBD	pF
C _{RSS}	V _{GS} = 0 V	V _{DS} = 26 V	f = 1 MHz		TBD	pF

Symbol	Test Conditions	Min.	Typ.	Max.	Unit
DYNAMIC (f = 2170 MHz)					
P _{out} ⁽¹⁾	V _{DD} = 26 V I _{DQ} = TBD	4	5		W
η _D ⁽¹⁾	V _{DD} = 26 V I _{DQ} = TBD	45	50		%
Load mismatch	V _{DD} = 26 V I _{DQ} = TBD P _{OUT} = 4 W ALL PHASE ANGLES			10:1	VSWR
DYNAMIC (f = 2110 - 2170 MHz)					
P _{out} ⁽¹⁾	V _{DD} = 26 V I _{DQ} = TBD	3	4		W
η _D ⁽¹⁾	V _{DD} = 26 V I _{DQ} = TBD	40	45		%
G _P	V _{DD} = 26 V I _{DQ} = TBD P _{OUT} = 4 W	11	13		dB
P _{OUT(W-CDMA)}	ACPR: -45dBc		1		W
η _{D(W-CDMA)}	ACPR: -45dBc		25		%

(1) 1 dB Compression point

PowerFLAT™ MECHANICAL DATA

DIM.	mm			Inch		
	MIN.	Typ.	MAX	MIN.	Typ.	MAX
A		0.90	1.00		0.035	0.039
A1		0.02	0.05		0.001	0.002
A3		0.24			0.009	
AA	0.15	0.25	0.35	0.006	0.01	0.014
b	0.43	0.51	0.58	0.017	0.020	0.023
c	0.64	0.71	0.79	0.025	0.028	0.031
D		5.00			0.197	
d		0.30			0.011	
E		5.00			0.197	
E2	2.49	2.57	2.64	0.098	0.101	0.104
e		1.27			0.050	
f		3.37			0.132	
g		0.74			0.03	
h		0.21			0.008	



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